

2SB857, 2SB858

Silicon PNP Triple Diffused

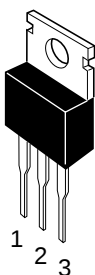
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Application

Low frequency power amplifier complementary pair with 2SD1133 and 2SD1134

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB857	2SB858	
Collector to base voltage	V_{CBO}	-70	-70	V
Collector to emitter voltage	V_{CEO}	-50	-60	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-4	-4	A
Collector peak current	$I_{C(peak)}$	-8	-8	A
Collector power dissipation	P_C^{*1}	40	40	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-45 to +150	-45 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

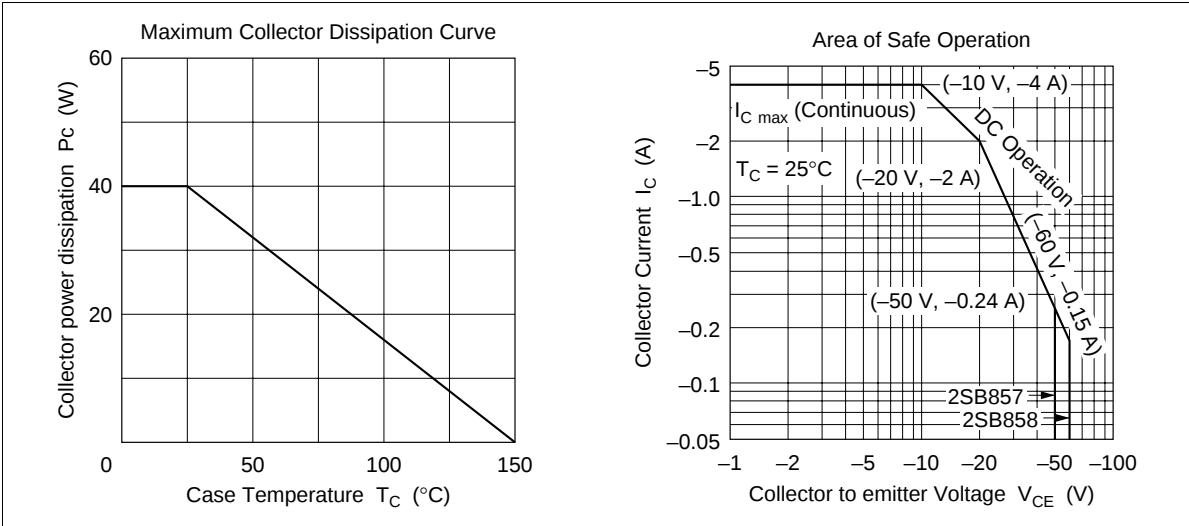
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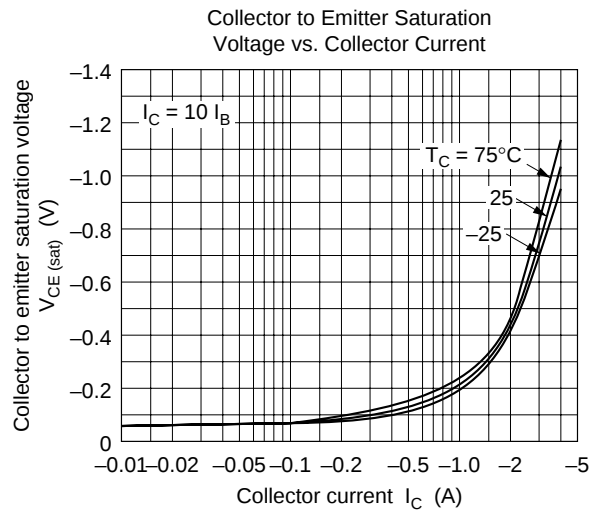
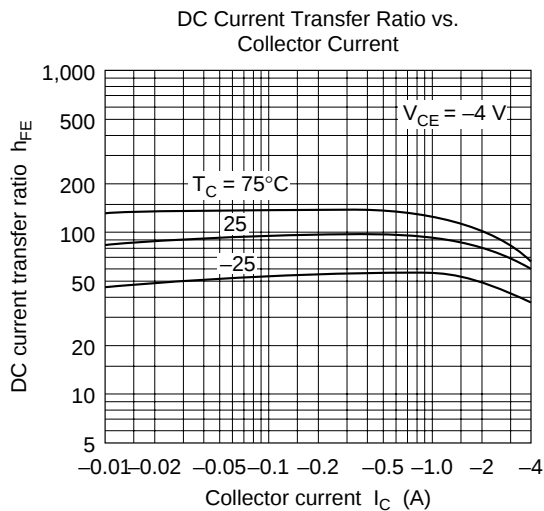
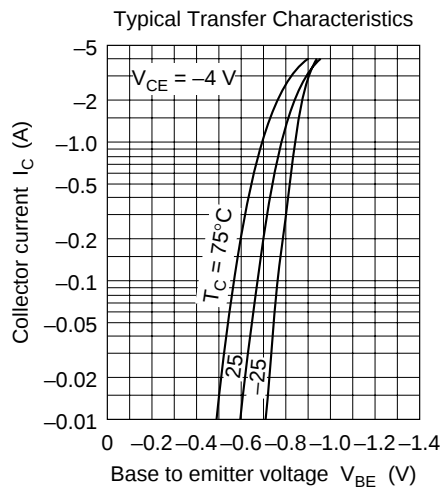
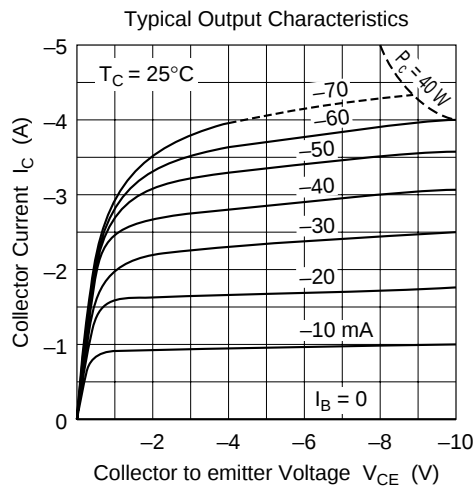
Electrical Characteristics (Ta = 25°C)

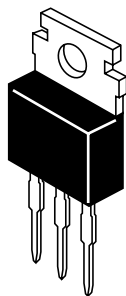
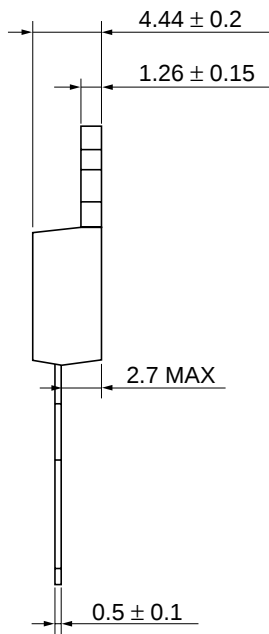
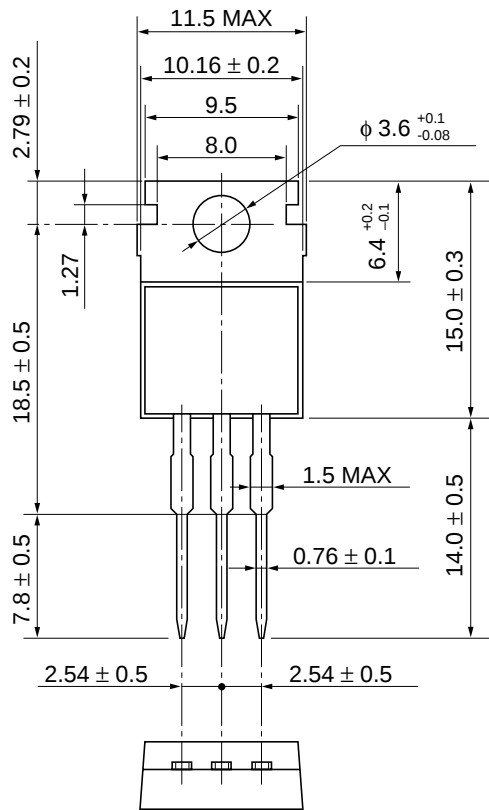
Item	Symbol	2SB857			2SB858			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	320		$V_{CE} =$ $I_C = -1\text{ A}^{*2}$
	h_{FE2}	35	—	—	35	—	—		-4 V $I_C = -0.1\text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -2\text{ A}$, $I_B = -0.2\text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1	—	—	-1	V	$V_{CE} = -4\text{ V}$, $I_C = -1\text{ A}^{*2}$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4\text{ V}$, $I_C = -0.5\text{ A}^{*2}$

Notes: 1. The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.
2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX
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